

GT50J327

Current Resonance Inverter Switching Application

- Enhancement mode type
- High speed : $t_f = 0.19 \mu s$ (typ.) ($I_C = 50A$)
- Low saturation voltage: $V_{CE(sat)} = 1.9 V$ (typ.) ($I_C = 50A$)
- FRD included between emitter and collector
- Fourth generation IGBT
- TO-3P(N) (Toshiba package name)

Maximum Ratings ($T_a = 25^\circ C$)

| Characteristics | Symbol | Rating | Unit |
|------------------------------|-----------------------|---------------|------------|
| Collector-emitter voltage | V_{CES} | 600 | V |
| Gate-emitter voltage | V_{GES} | ± 25 | V |
| Continuous collector current | @ $T_c = 100^\circ C$ | 29 | A |
| | @ $T_c = 25^\circ C$ | 50 | |
| Pulsed collector current | I_{CP} | 100 | A |
| Diode forward current | DC | $I_F = 20$ | A |
| | Pulsed | $I_{FP} = 40$ | |
| Collector power dissipation | @ $T_c = 100^\circ C$ | 56 | W |
| | @ $T_c = 25^\circ C$ | 140 | |
| Junction temperature | T_j | 150 | $^\circ C$ |
| Storage temperature range | T_{stg} | -55 to 150 | $^\circ C$ |

Unit: mm

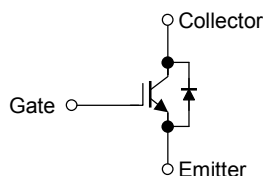
| | |
|---------|---------|
| JEDEC | — |
| JEITA | — |
| TOSHIBA | 2-16C1C |

Weight: 4.6 g (typ.)

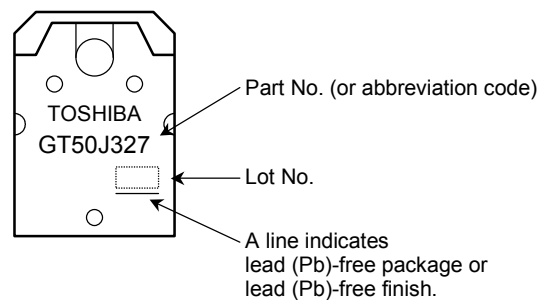
Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|----------------------------|---------------|------|--------------|
| Thermal resistance (IGBT) | $R_{th(j-c)}$ | 0.89 | $^\circ C/W$ |
| Thermal resistance (diode) | $R_{th(j-c)}$ | 2.7 | $^\circ C/W$ |

Equivalent Circuit



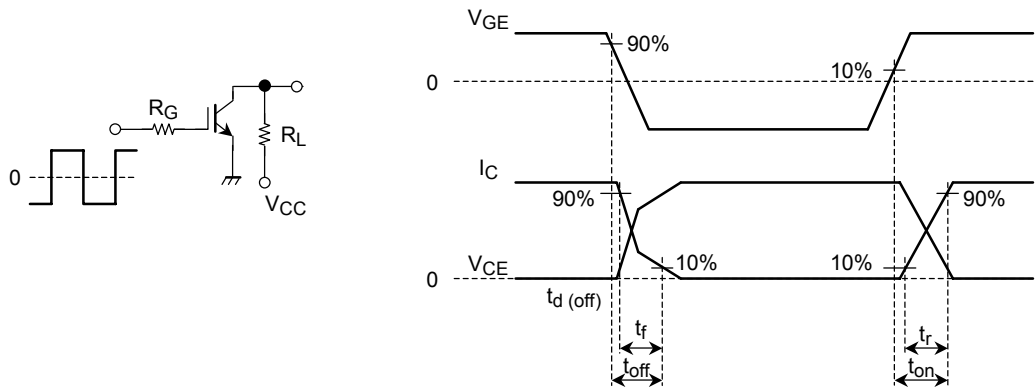
Marking

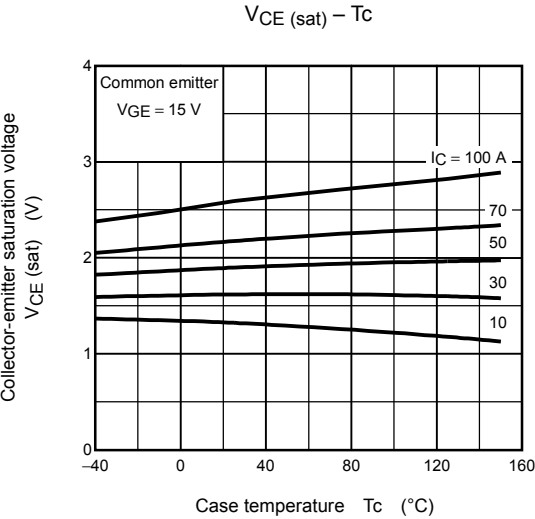
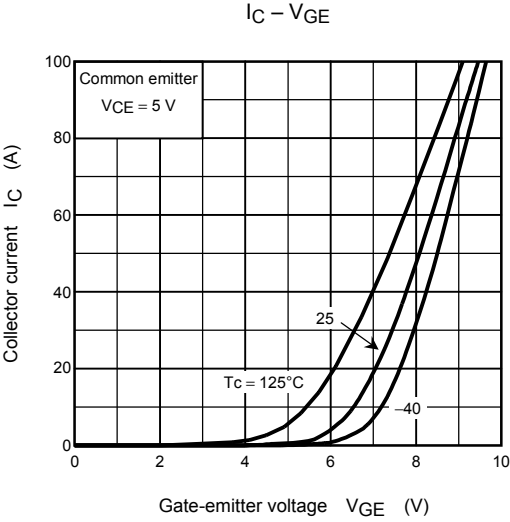
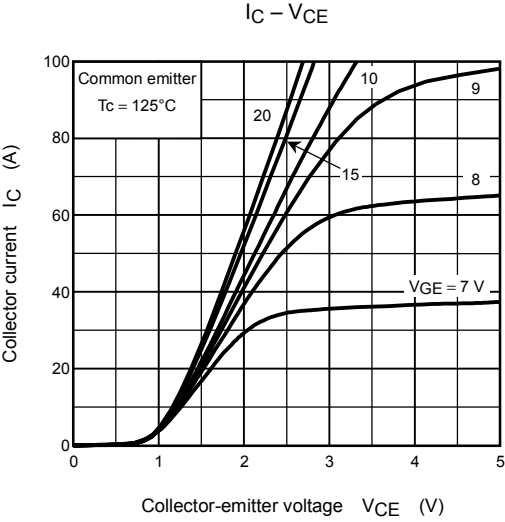
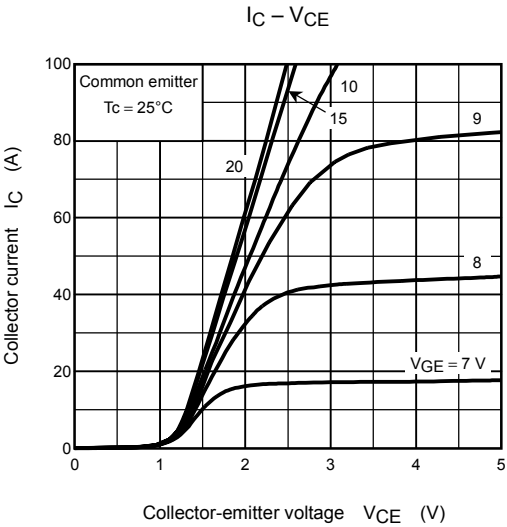
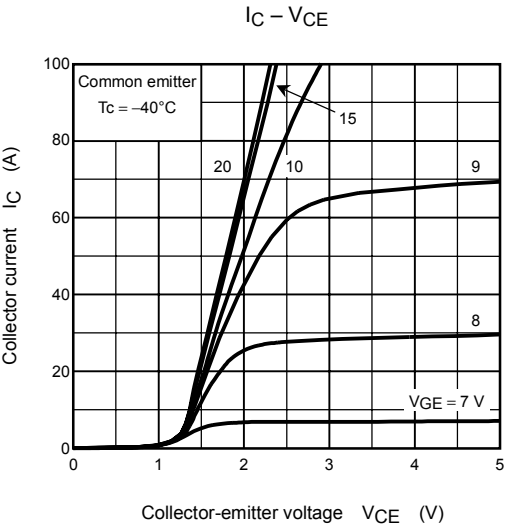


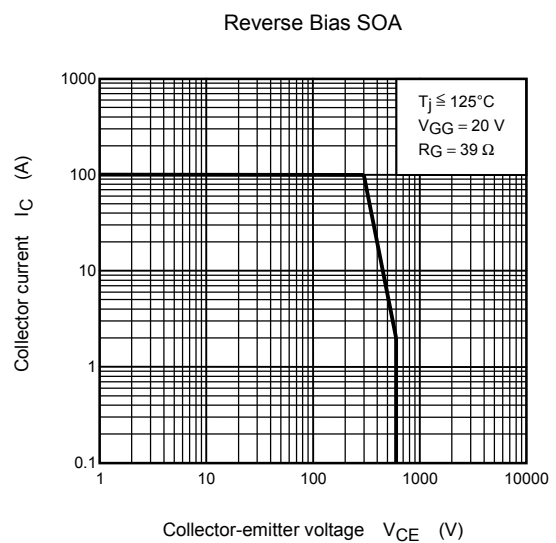
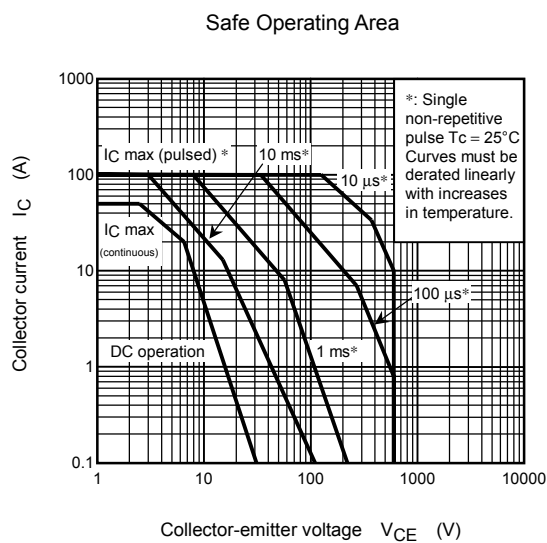
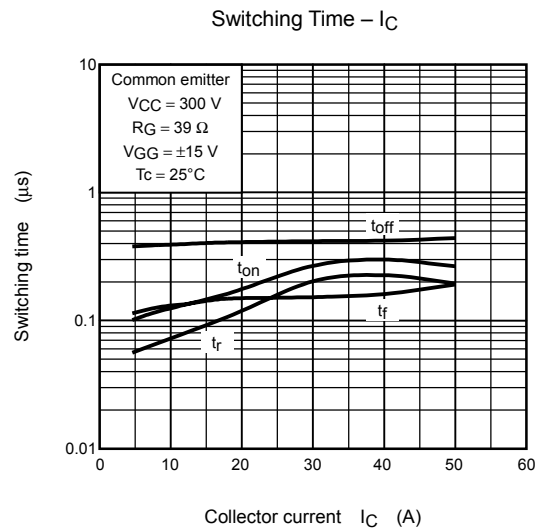
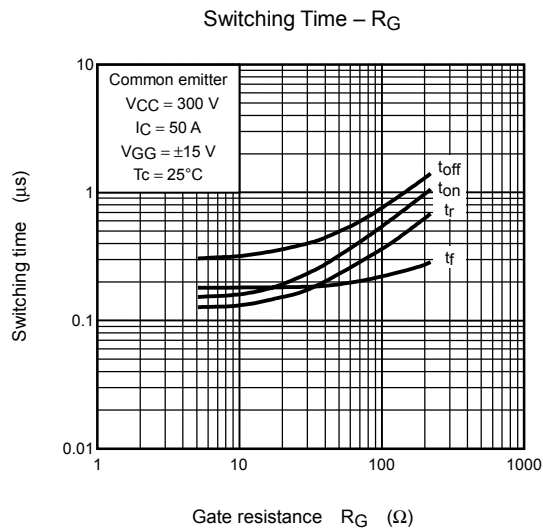
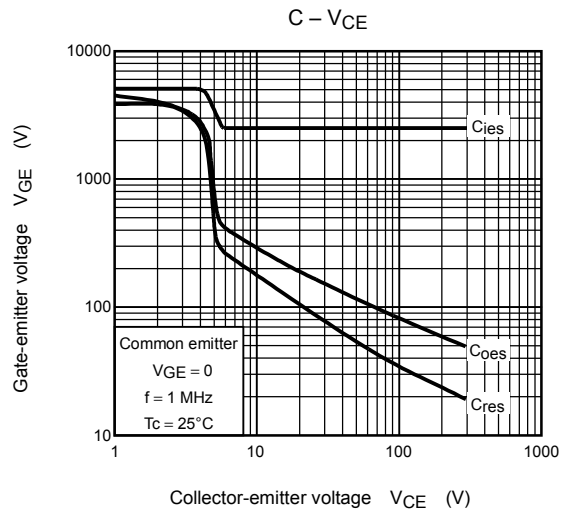
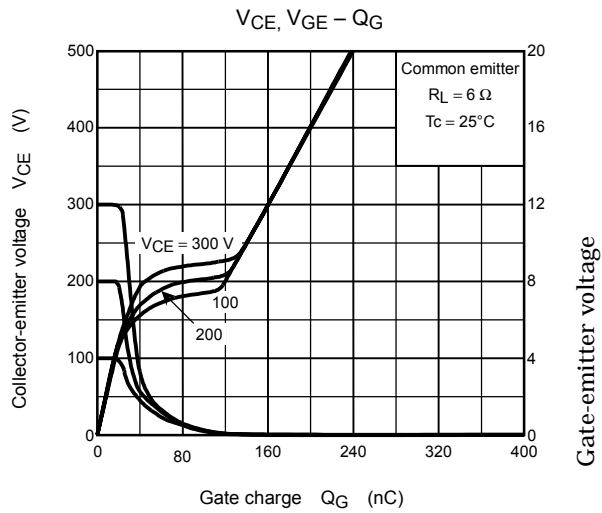
Electrical Characteristics (Ta = 25°C)

| Characteristics | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--------------------------------------|---------------|----------------------|--|-----|------|-----------|---------------|
| Gate leakage current | | I_{GES} | $V_{GE} = \pm 25\text{ V}, V_{CE} = 0$ | — | — | ± 500 | nA |
| Collector cut-off current | | I_{CES} | $V_{CE} = 600\text{ V}, V_{GE} = 0$ | — | — | 1.0 | mA |
| Gate-emitter cut-off voltage | | $V_{GE(\text{OFF})}$ | $I_C = 50\text{ mA}, V_{CE} = 5\text{ V}$ | 3.0 | — | 6.0 | V |
| Collector-emitter saturation voltage | | $V_{CE(\text{sat})}$ | $I_C = 50\text{ A}, V_{GE} = 15\text{ V}$ | — | 1.9 | 2.3 | V |
| Input capacitance | | C_{ies} | $V_{CE} = 10\text{ V}, V_{GE} = 0, f = 1\text{ MHz}$ | — | 2500 | — | pF |
| Switching time | Rise time | t_r | Resistive Load $V_{CC} = 300\text{ V}, I_C = 50\text{ A}$ $V_{GG} = \pm 15\text{ V}, R_G = 39\ \Omega$ (Note 1) | — | 0.20 | — | μs |
| | Turn-on time | t_{on} | | — | 0.27 | — | |
| | Fall time | t_f | | — | 0.19 | 0.32 | |
| | Turn-off time | t_{off} | | — | 0.44 | — | |
| Diode forward voltage | | V_F | $I_F = 15\text{ A}, V_{GE} = 0$ | — | — | 2.0 | V |
| Reverse recovery time | | t_{rr} | $I_F = 15\text{ A}, di/dt = -100\text{ A}/\mu\text{s}$ | — | — | 0.2 | μs |

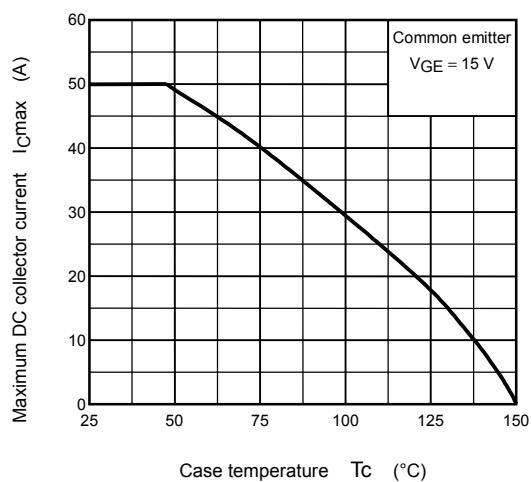
Note 1: Switching time measurement circuit and input/output waveforms



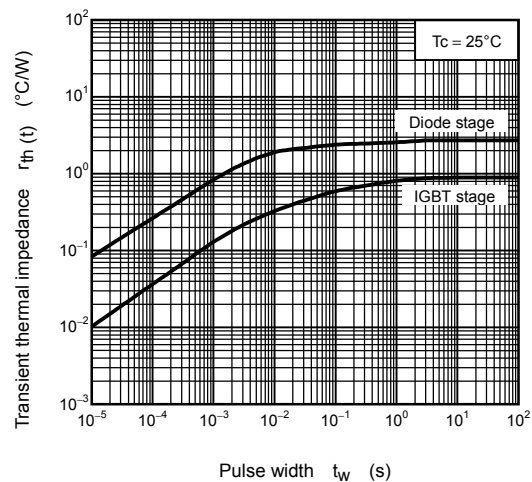




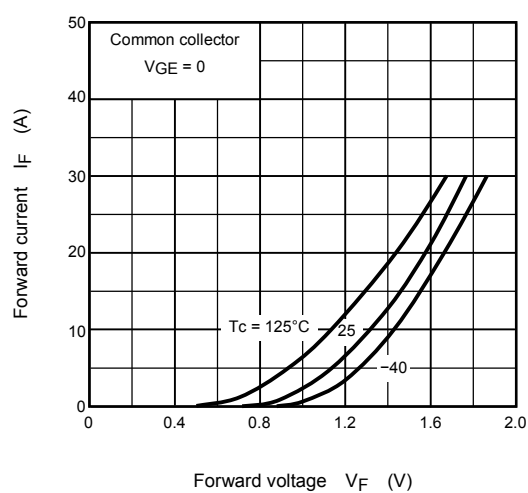
$I_{Cmax} - T_c$



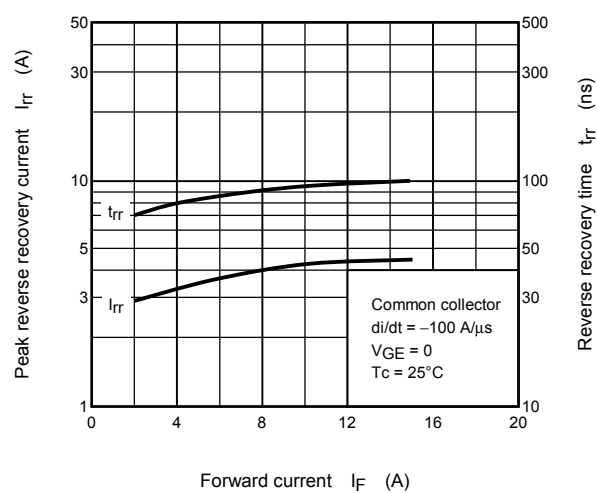
$r_{th}(t) - t_w$



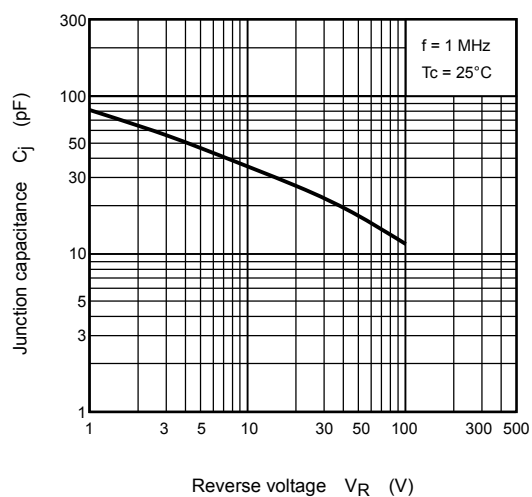
$I_F - V_F$



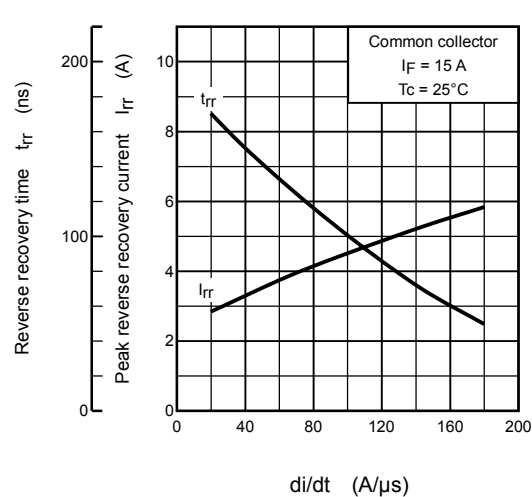
$I_{rr}, t_{rr} - I_F$



$C_j - V_R$



$I_{rr}, t_{rr} - di/dt$



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